


International  
**IR** Rectifier

**SERIES**  
**IRK.136, .142, .162**

**THYRISTOR/DIODE and**  
**THYRISTOR/THYRISTOR**

**NEW INT-A-pak Power Modules**

#### Features

- High Voltage
- Electrically Isolated by DBC Ceramic ( $Al_2O_3$ )
- 3500  $V_{RMS}$  Isolating Voltage
- Industrial Standard Package
- High Surge Capability
- Glass Passivated Chips
- Modules uses High Voltage Power thyristor/diodes in three Basic Configurations
- Simple Mounting
- UL E78996 approved 

135 A  
 140 A  
 160 A

#### Applications

- DC Motor Control and Drives
- Battery Charges
- Welders
- Power Converters
- Lighting Control
- Heat and Temperature Control

#### Major Ratings and Characteristics

Parameters	IRK.136..	IRK.142..	IRK.162..	Units
$I_{T(AV)}$	135	140	160	A
@ $T_C$	85	85	85	°C
$I_{T(RMS)}$	300	310	355	A
$I_{TSM}$ @ 50Hz	3200	4500	4870	A
@ 60Hz	3360	4712	5100	A
$I^2t$ @ 50Hz	51.5	102	119	KA <sup>2</sup> s
@ 60Hz	47	92.5	108	KA <sup>2</sup> s
$I^2\sqrt{t}$	515.5	1013	1190	KA <sup>2</sup> √s
$V_{RRM}$	400 to 1600			V
$T_J$ range	-40 to 125			°C

CASE STYLE NEW INT-A-PAK



**Electrical Specifications**

**Voltage Ratings**

Type number	Voltage Code	$V_{RRM}/V_{DRM}$ , Maximum repetitive peak reverse voltage V	$V_{RSM}/V_{DSM}$ , Maximum non-repetitive peak reverse voltage V	$I_{RRM}/I_{DRM}$ @ 125°C mA
IRK.136	04	400	500	50
IRK.142	08	800	900	
IRK.162	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

**Forward Conduction**

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Case temperature	135	140	160	A	180° conduction, half sine wave
	85	85	85	°C	
$I_{T(RMS)}$ Max. RMS on-state current	300	310	355	A	as AC switch
$I_{TSM}$ Maximum peak, one-cycle on-state, non-repetitive surge current	3200	4500	4870	A	t = 10ms No voltage
	3360	4712	5100		t = 8.3ms reapplied
	2700	3785	4100		t = 10ms 100% $V_{RRM}$
	2800	3963	4300		t = 8.3ms reapplied
$I^2t$ Maximum $I^2t$ for fusing	51.5	102	119	KA <sup>2</sup> s	t = 10ms No voltage
	47	92.5	108		t = 8.3ms reapplied
	36.5	71.6	84		t = 10ms 100% $V_{RRM}$
	33.3	65.4	76.7		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	515.5	1013	1190	KA <sup>2</sup> /s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.86	0.83	0.8	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , @ $T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	1.05	1	0.98	V	$(I > \pi \times I_{T(AV)})$ , @ $T_J$ max.
$r_{T1}$ Low level value on-state slope resistance	2.02	1.78	1.67	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , @ $T_J$ max.
$r_{T2}$ High level value on-state slope resistance	1.65	1.43	1.38	mΩ	$(I > \pi \times I_{T(AV)})$ , @ $T_J$ max.
$V_{TM}$ Maximum forward voltage drop	1.57	1.55	1.54	V	$I_{TM} = \pi \times I_{T(AV)}$ , $T_J = 25^\circ\text{C}$ , 180° conduction
$I_H$ Maximum holding current	200			mA	Anode supply = 6V initial $I_T = 30A$ , $T_J = 25^\circ\text{C}$
$I_L$ Maximum latching current	400			mA	Anode supply = 6V resistive load = 1Ω Gate pulse: 10V, 100μs, $T_J = 25^\circ\text{C}$

**Switching**

$t_{gd}$ Typical delay time	1	μs	$T_J = 25^\circ\text{C}$	Gate Current=1A $di/dt=1A/\mu\text{s}$
$t_{gr}$ Typical rise time	2		$T_J = 25^\circ\text{C}$	$V_d=0.67\% V_{DRM}$
$t_q$ Typical turn-off time	50 - 200		$I_{TM} = 300A$ ; $-di/dt = 15A/\mu\text{s}$ ; $T_J = T_J \text{ max}$ $V_T = 50V$ ; $dV/dt = 20V/\mu\text{s}$ ; Gate 0V, 100Ω	

Blocking

$I_{RRM}$	Maximum peak reverse and off-state leakage current	50	mA	$T_J = 125^\circ\text{C}$
$V_{INS}$	RMS isolation voltage	3500	V	50Hz, circuit to base, all terminals shorted, $t = 1\text{s}$
$dV/dt$	critical rate of rise of off-state voltage	1000	V/ $\mu\text{s}$	$T_J = T_{J\text{max.}}$ , exponential to 67% rated $V_{DRM}$

Triggering

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions
$P_{GM}$	12			W	$t_p \leq 5\text{ms}$ , $T_J = T_{J\text{max.}}$
$P_{G(AV)}$	3			W	$f = 50\text{Hz}$ , $T_J = T_{J\text{max.}}$
$I_{GM}$	3			A	$t_p \leq 5\text{ms}$ , $T_J = T_{J\text{max.}}$
$-V_{GT}$	10			V	
$V_{GT}$	Max. required DC gate voltage to trigger	4		V	$T_J = -40^\circ\text{C}$
		2.5			$T_J = 25^\circ\text{C}$
		1.7			$T_J = T_{J\text{max.}}$
$I_{GT}$	Max. required DC gate current to trigger	270		mA	$T_J = -40^\circ\text{C}$
		150			$T_J = 25^\circ\text{C}$
		80			$T_J = T_{J\text{max.}}$
$V_{GD}$	0.3			V	@ $T_J = T_{J\text{max.}}$ , rated $V_{DRM}$ applied
$I_{GD}$	10			mA	
$di/dt$	300			A/ $\mu\text{s}$	@ $T_J = T_{J\text{max.}}$ , $I_{TM} = 400\text{A}$ rated $V_{DRM}$ applied

Thermal and Mechanical Specifications

Parameter	IRK.136	IRK.142	IRK.162	Units	Conditions
$T_J$	-40 to 125			$^\circ\text{C}$	
$T_{stg}$	-40 to 150			$^\circ\text{C}$	
$R_{thJC}$	0.18	0.18	0.16	K/W	DC operation, per junction
$R_{thCS}$	0.05			K/W	Mounting surface smooth, flat and greased Per module
T	Mounting IAP to heatsink	4 to 6		Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. Lubricated threads.
	torque $\pm 10\%$ busbar to IAP	4 to 6			
wt	200 (7.1)			g(oz)	
Case Style	New Int-A-Pak				

$\Delta R$  Conduction (per Junction)

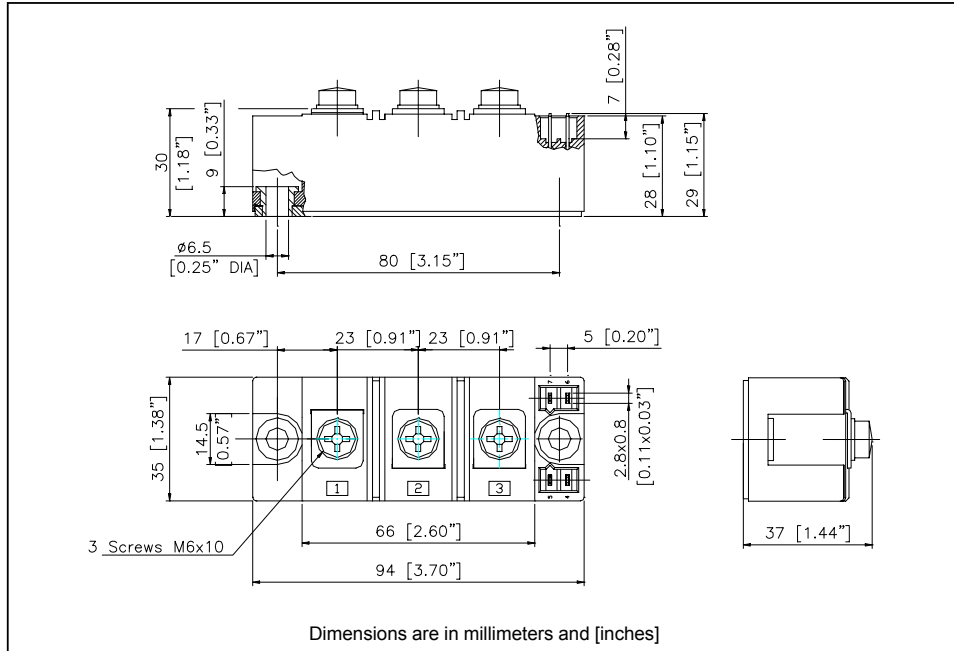
(The following table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC)

Devices	Sinusoidal conduction @ $T_J$ max.					Rectangular conduction @ $T_J$ max.					Units
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
IRK.136	0.007	0.01	0.013	0.0155	0.017	0.009	0.012	0.014	0.015	0.017	K/W
IRK.142	0.0019	0.0019	0.0020	0.0020	0.0021	0.0018	0.0022	0.0023	0.0023	0.0020	
IRK.162	0.0030	0.0031	0.0032	0.0033	0.0034	0.0029	0.0036	0.0039	0.0041	0.0040	

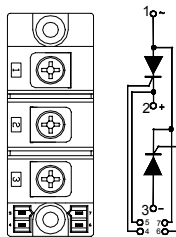
Ordering Information Table

Device Code				
IRK	T	162	/	16
①	②	③		④
<b>1</b>	- Module Type			
<b>2</b>	- Circuit Configuration			
<b>3</b>	- Current Rating: $I_{T(AV)}$			
<b>4</b>	- Voltage Code: Code x 100 = $V_{RRM}$			

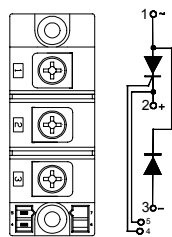
Outline Table



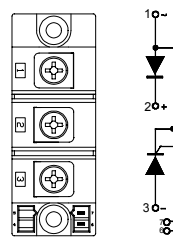
**IRKT**



**IRKH**



**IRKL**



**NOTE:** To order the Optional Hardware see Bulletin I27900

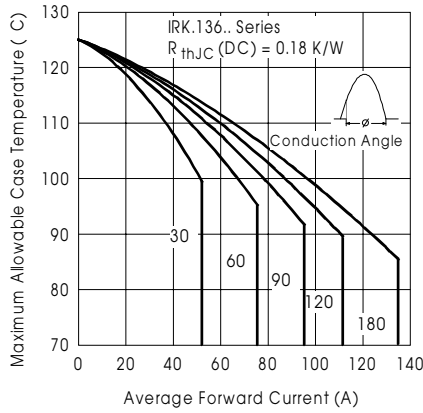


Fig. 1 - Current Ratings Characteristics

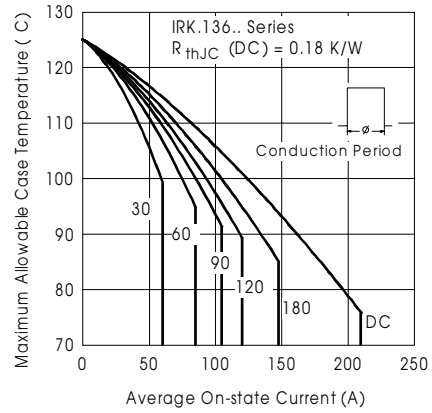


Fig. 2 - Current Ratings Characteristics

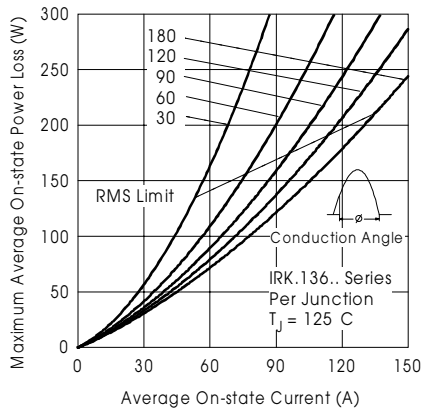


Fig. 3 - On-State Power Loss Characteristics

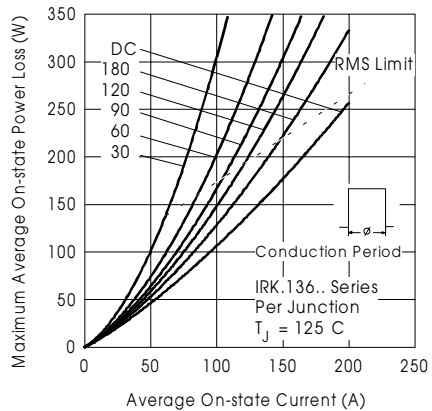


Fig. 4 - On-State Power Loss Characteristics

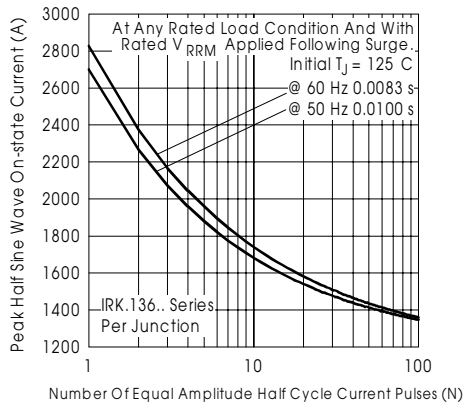


Fig. 5 - Maximum Non-Repetitive Surge Current

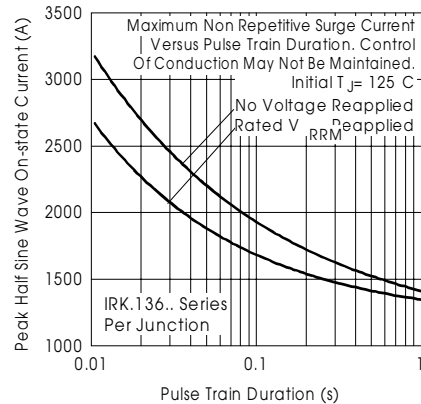


Fig. 6 - Maximum Non-Repetitive Surge Current

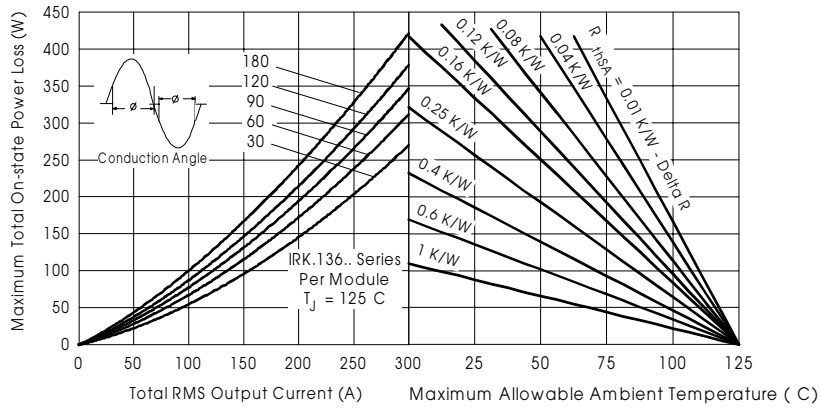


Fig.7 - On State Power Loss Characteristics

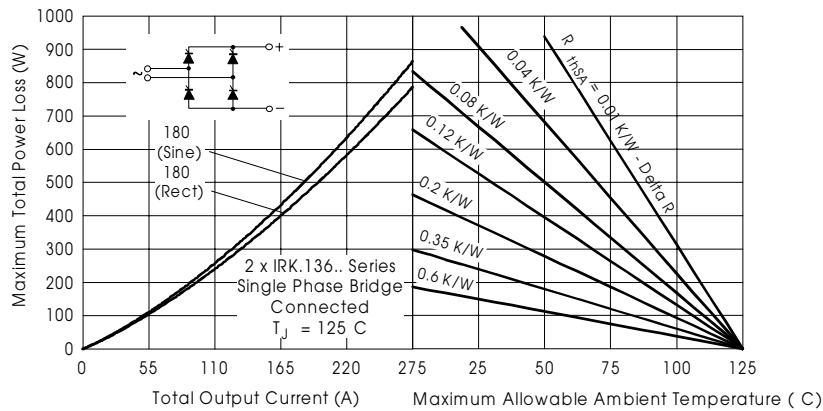


Fig.8 - On State Power Loss Characteristics

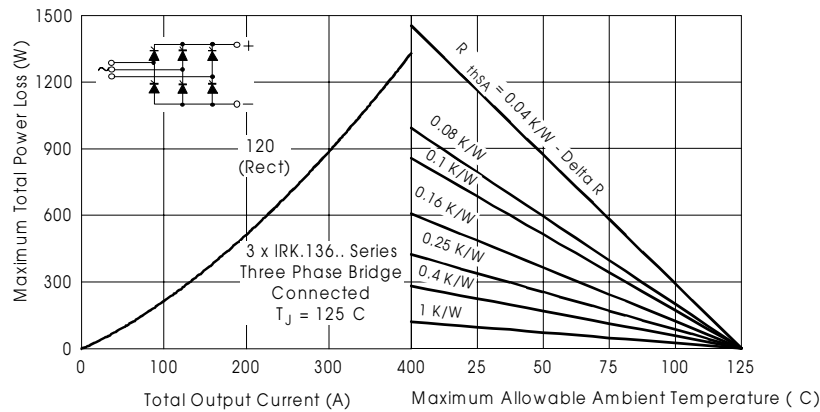


Fig.9 - On State Power Loss Characteristics

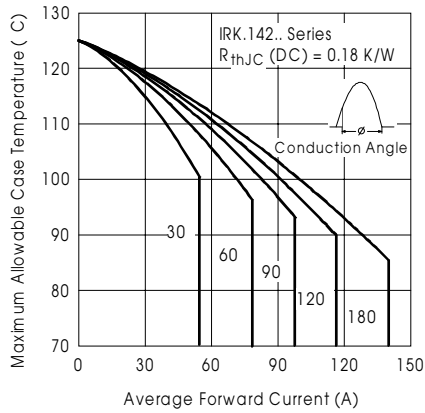


Fig. 10 - Current Ratings Characteristics

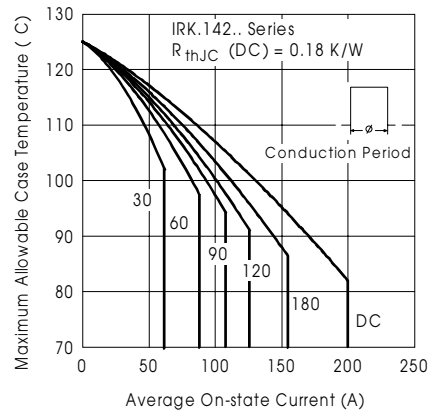


Fig. 11 - Current Ratings Characteristics

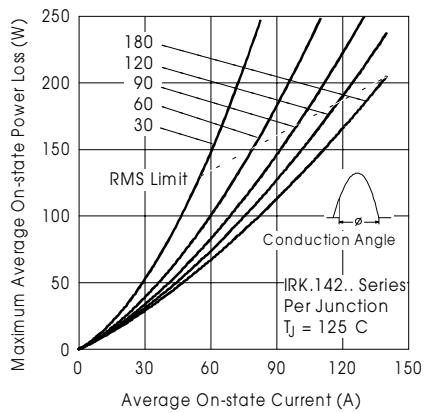


Fig. 12 - On-State Power Loss Characteristics

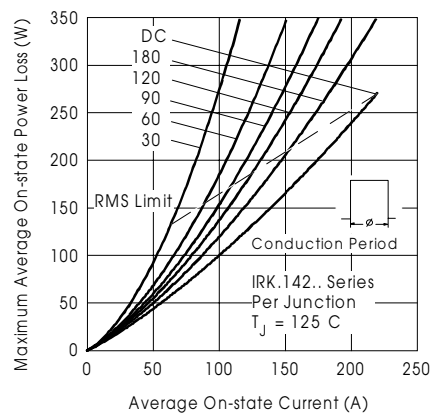


Fig. 13 - On-State Power Loss Characteristics

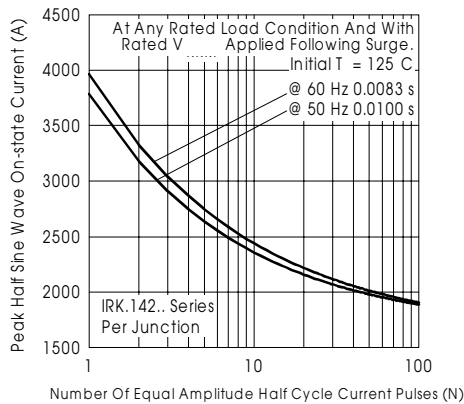


Fig. 14 - Maximum Non-Repetitive Surge Current

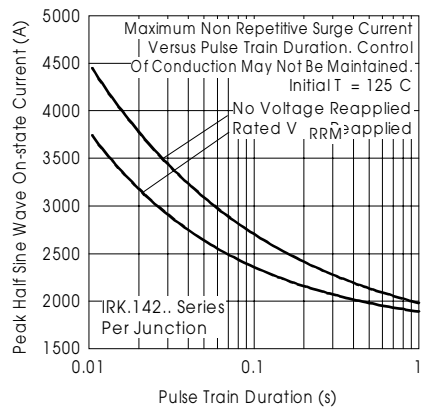


Fig. 15 - Maximum Non-Repetitive Surge Current

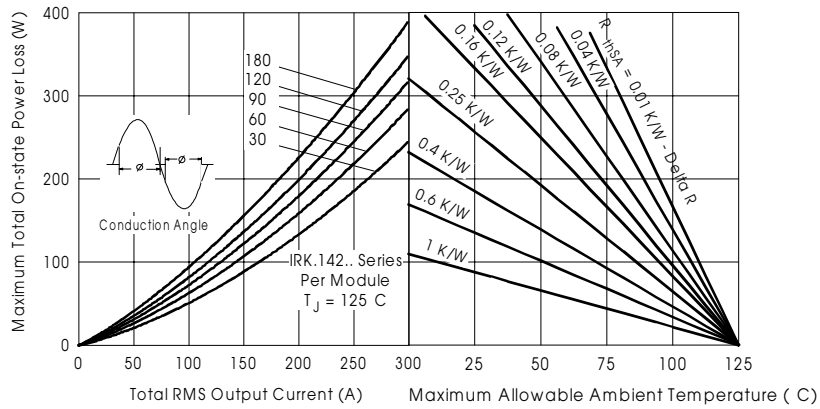


Fig.16 - On State Power Loss Characteristics

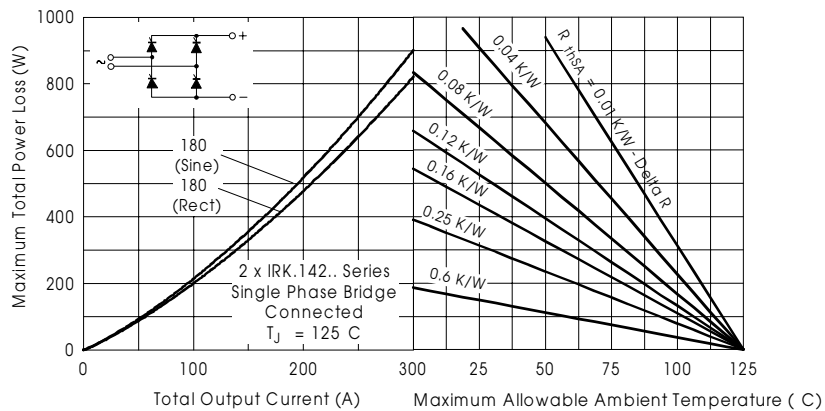


Fig.17 - On State Power Loss Characteristics

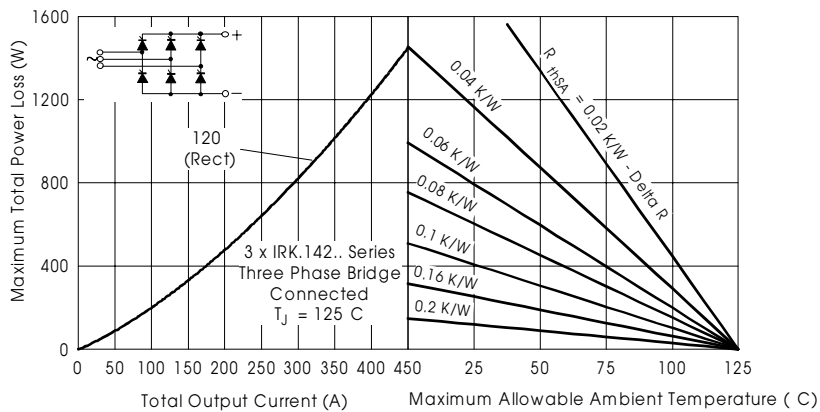


Fig.18 - On State Power Loss Characteristics



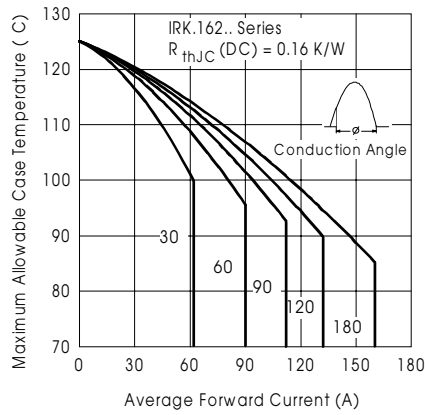


Fig. 19 - Current Ratings Characteristics

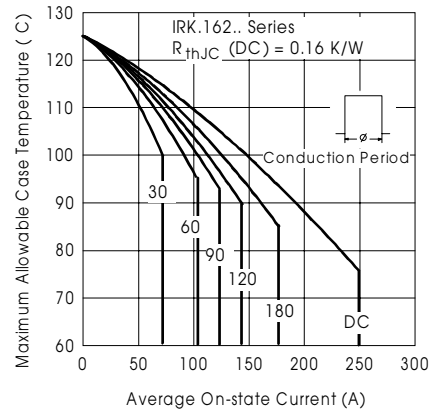


Fig. 20 - Current Ratings Characteristics

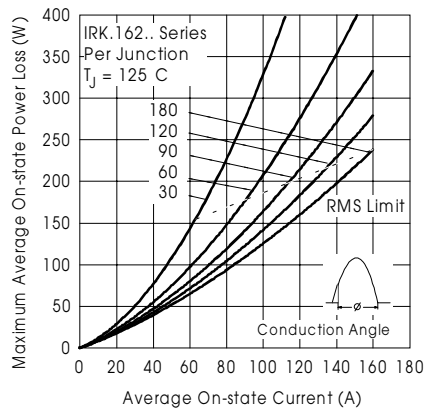


Fig. 21 - On-State Power Loss Characteristics

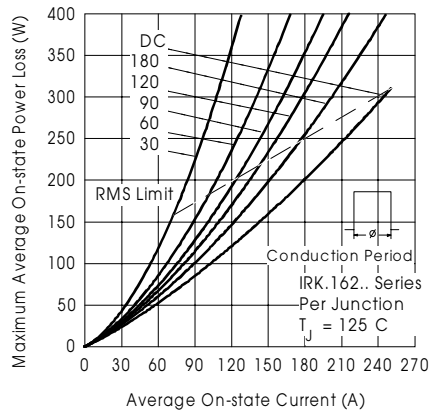


Fig. 22 - On-State Power Loss Characteristics

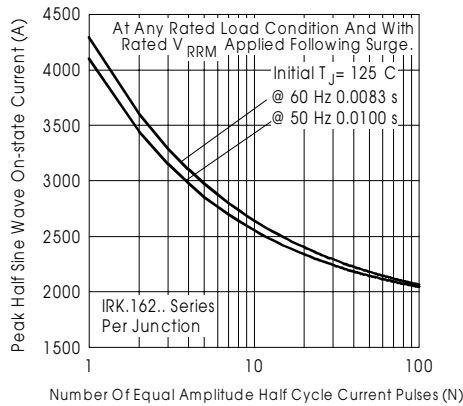


Fig. 23 - Maximum Non-Repetitive Surge Current

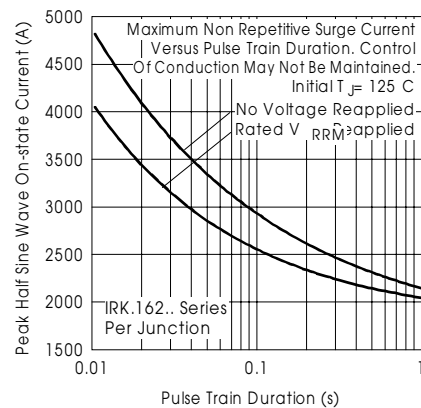


Fig. 24 - Maximum Non-Repetitive Surge Current

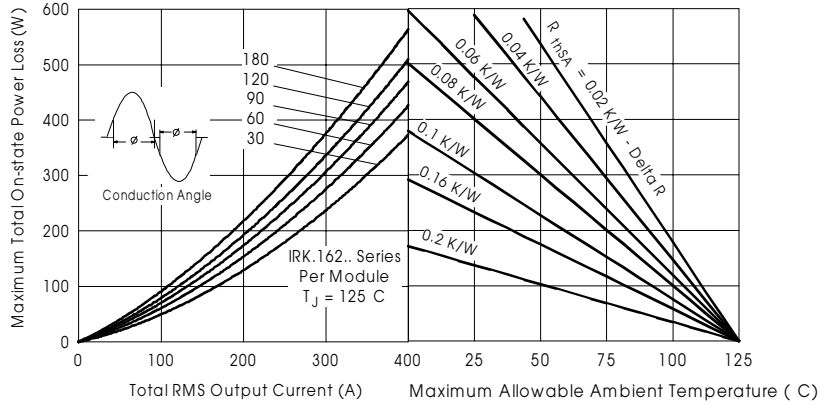


Fig.25- On State Power Loss Characteristics

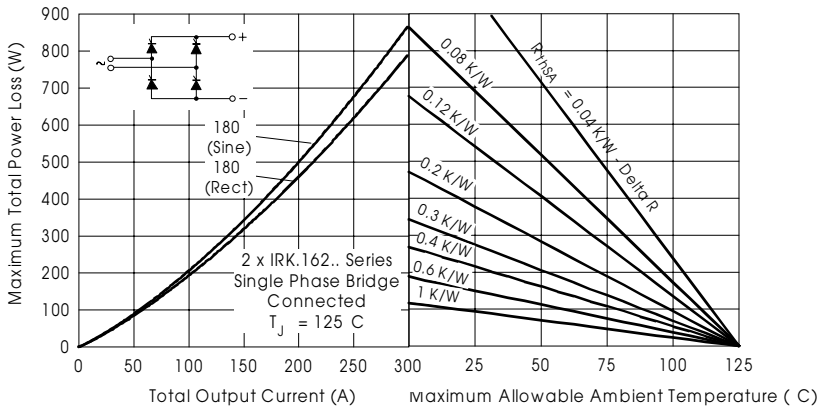


Fig.26- On State Power Loss Characteristics

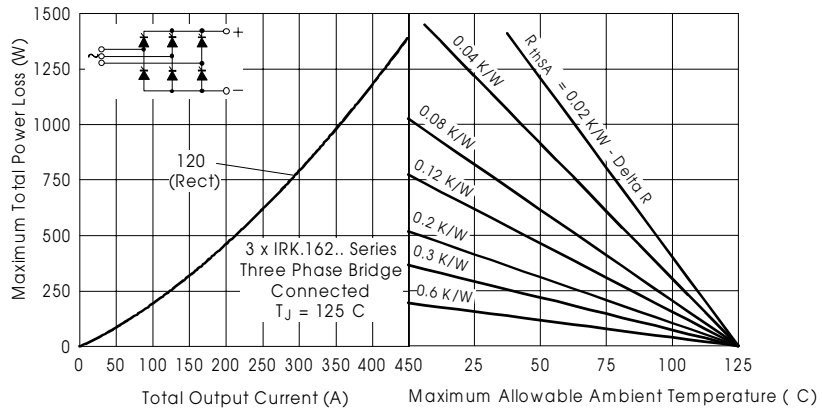


Fig.27- On State Power Loss Characteristics

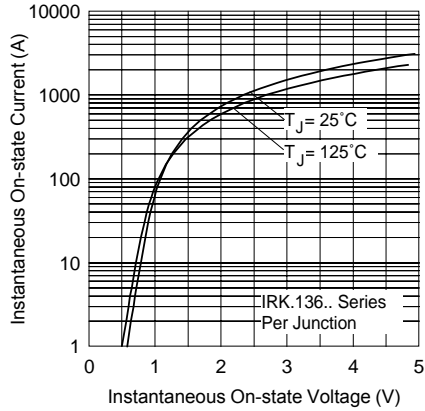


Fig.28 - On State Voltage Drop Characteristics

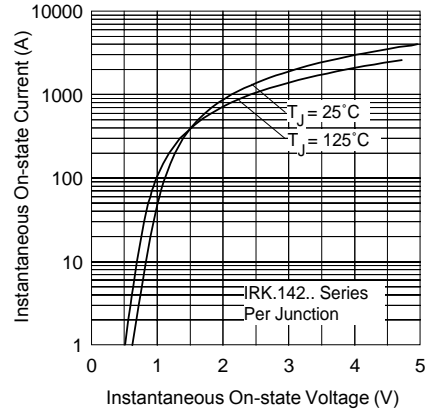


Fig.29 - On State Voltage Drop Characteristics

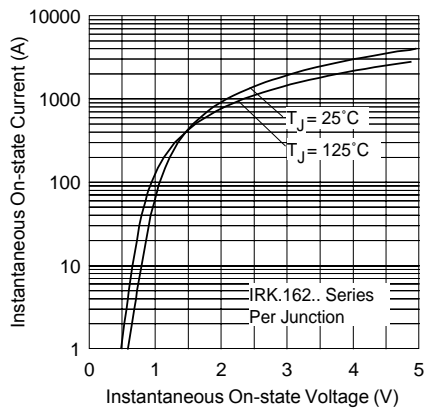


Fig.30 - On State Voltage Drop Characteristics

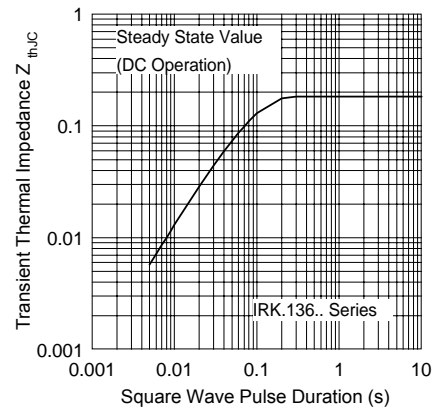


Fig.31 - Thermal Impedance ZthJC Characteristics

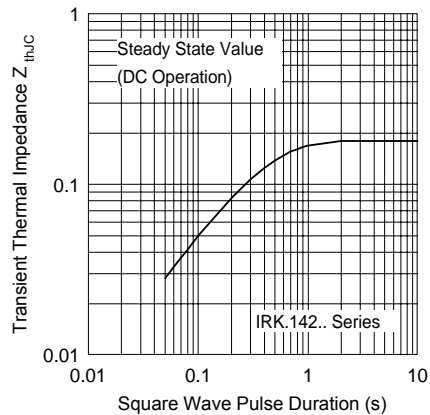


Fig.32 - Thermal Impedance ZthJC Characteristics

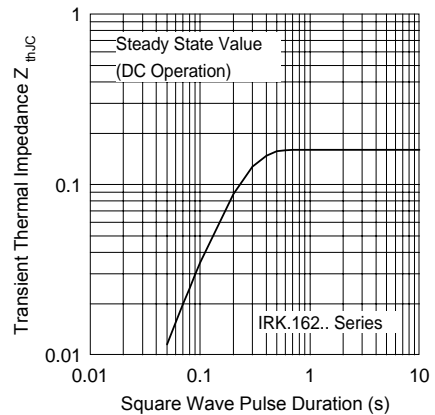


Fig.33 - Thermal Impedance ZthJC Characteristics

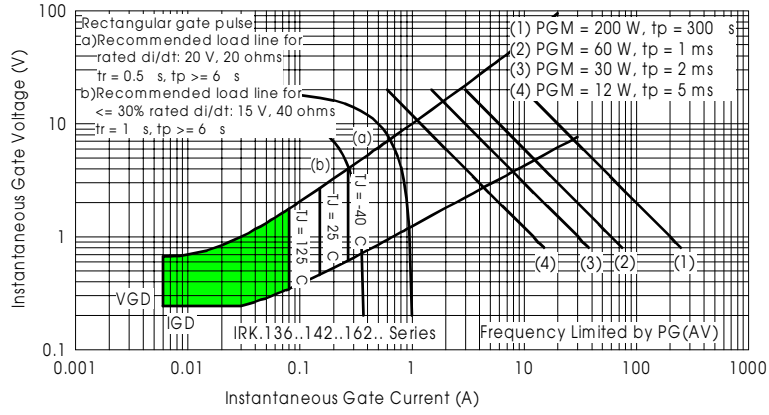


Fig. 34 - Gate Characteristics

Data and specifications subject to change without notice.  
This product has been designed and qualified for Multiple Level.  
Qualification Standards can be found on IR's Web site.